

### Schottky Barrier Diodes

**(Pb)** Lead(Pb)-Free

#### Features:

- \* High Reliability
- \* Low Reverse Current and Low Forward Voltage

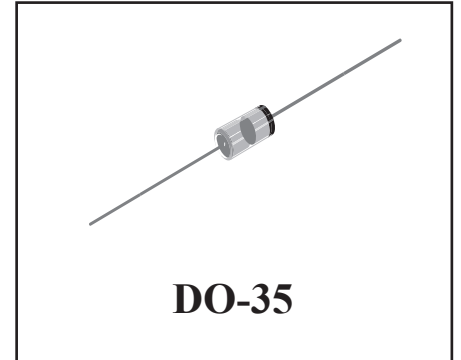
#### Applications:

- \* Low Current Rectification and High Speed Switching

#### Mechanical Data:

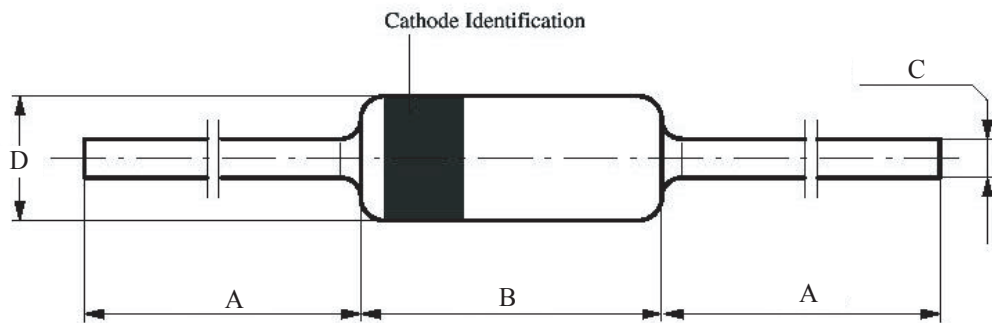
- \*Case : DO-35 Glass Case
- \*Weight : Approx 0.13 gram

**SMALL SIGNAL  
SCHOTTKY DIODES  
30m/50m AMPERES  
40/45VOLTS**



## DO-35 Outline Dimensions

Unit:mm



DIM	A		B		C		D	
	Min	Max	Min	Max	Min	Max	Min	Max
DO-35	26.0	-	-	4.20	-	0.55	-	2.0

## Maximum Ratings (T<sub>A</sub>=25°C Unless otherwise noted)

Characteristic	Symbol	1N60	1N60P	Unit
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	40	45	V
Forward Continuous Current	I <sub>F</sub>	30	50	mA
Peak Forward Surge Current (t <sub>p</sub> ≤1s)	I <sub>FSM</sub>	150	500	mA
Thermal Resistance Junction to Ambient <sup>(1)</sup>	R <sub>θJA</sub>	250		K/W
Operating Temperature Range	T <sub>J</sub>	125		°C
Storage Temperature Range	T <sub>STG</sub>	-65 to +125		°C

1. On PC board 50mm x 50mm x 1.6mm

## Electrical Characteristics (T<sub>A</sub>=25°C Unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit	
Forward Voltage I <sub>F</sub> =1mA	V <sub>F</sub>	-	1N60	0.32	0.5	V
			1N60P	0.24	0.5	
I <sub>F</sub> =30mA			1N60	0.65	1.0	
I <sub>F</sub> =200mA			1N60P	0.65	1.0	
Reverse Current V <sub>R</sub> =15V	I <sub>R</sub>	-	1N60 0.1	1N60P 0.5	0.5 1.0	μA
Junction Capacitance V <sub>R</sub> =1V, f=1MHz	C <sub>J</sub>	-	1N60	2.0	-	pF
V <sub>R</sub> =10V, f=1MHz			1N60P	6.0		
Reverse Recovery Time I <sub>F</sub> =I <sub>R</sub> =1mA, I <sub>rr</sub> =1mA, R <sub>C</sub> =100Ω	T <sub>rr</sub>	-	-	1.0	nS	